

Hirokazu Fukidome

List of Publications by Year in descending order

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59
papers

1,236
citations

394421

19
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docs citations

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times ranked

1239
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#	ARTICLE	IF	CITATIONS
1	Creation of Affordable Manufacturing Processes of Ultrahigh-quality Graphene Growth and High-frequency Graphene Devices by Using Single-crystalline SiC Thin Films on Device-type Substrates. <i>Vacuum and Surface Science</i> , 2021, 64, 318-323.	0.1	0
2	A graphene-based magnetoplasmonic metasurface for actively tunable transmission and polarization rotation at terahertz frequencies. <i>Applied Physics Letters</i> , 2020, 116, 221107.	3.3	15
3	Electrical transport properties of gate tunable graphene lateral tunnel diodes. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SIID03.	1.5	3
4	Dynamics of surface electron trapping of a GaN-based transistors revealed by spatiotemporally resolved x-ray spectroscopy. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	9
5	Atomically Controlled Surfaces, Interfaces and Nanostructures/Scanning Probe Microscopy. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SI0001.	1.5	0
6	Ultrafast Unbalanced Electron Distributions in Quasicrystalline 30° Twisted Bilayer Graphene. <i>ACS Nano</i> , 2019, 13, 11981-11987.	14.6	28
7	Influence of interface dipole layers on the performance of graphene field effect transistors. <i>Carbon</i> , 2019, 152, 680-687.	10.3	19
8	Element- and Site-Specific Many-Body Interactions in Few-Layer MoS ₂ During X-Ray Absorption Processes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800539.	1.8	6
9	Operando Soft X-Ray Spectromicroscopic Measurement and the Use for High-Performance Devices and Circuits. , 2019, , 199-216.		0
10	Direct Formation of Solution-based Al ₂ O ₃ on Epitaxial Graphene Surface for Sensor Applications. <i>Sensors and Materials</i> , 2019, 31, 2291.	0.5	2
11	Modulation of Electronic States near Electrodes in Graphene Transistors Observed by Operando Photoelectron Nanospectroscopy. <i>Sensors and Materials</i> , 2019, 31, 2303.	0.5	1
12	A table-top formation of bilayer quasi-free-standing epitaxial-graphene on SiC(0001) by microwave annealing in air. <i>Carbon</i> , 2018, 130, 792-798.	10.3	14
13	Operation Mechanism of GaN-based Transistors Elucidated by Element-Specific X-ray Nanospectroscopy. <i>Scientific Reports</i> , 2018, 8, 13268.	3.3	9
14	Enhancement of CO ₂ adsorption on oxygen-functionalized epitaxial graphene surface under near-ambient conditions. <i>Physical Chemistry Chemical Physics</i> , 2018, 20, 19532-19538.	2.8	19
15	Adsorption of CO ₂ on Graphene: A Combined TPD, XPS, and vdW-DF Study. <i>Journal of Physical Chemistry C</i> , 2017, 121, 2807-2814.	3.1	76
16	Fabrication of multi-layer Bi ₂ Se ₃ devices and observation of anomalous electrical transport behaviors. <i>Materials Science in Semiconductor Processing</i> , 2017, 68, 128-132.	4.0	8
17	Extremely uniform epitaxial growth of graphene from sputtered SiC films on SiC substrates. <i>MRS Advances</i> , 2017, 2, 51-56.	0.9	3
18	Inhomogeneous longitudinal distribution of Ni atoms on graphene induced by layer-number-dependent internal diffusion. <i>Applied Physics Letters</i> , 2016, 109, 111604.	3.3	1

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19	Observation of nanoscopic charge-transfer region at metal/MoS ₂ interface. Materials Research Express, 2016, 3, 075004.	1.6	5
20	Photonic Frequency Double-Mixing Conversion Over the 120-GHz Band Using InP- and Graphene-Based Transistors. Journal of Lightwave Technology, 2016, 34, 2011-2019.	4.6	14
21	Formation of qualified epitaxial graphene on Si substrates using two-step heteroepitaxy of C-terminated 3C-SiC(-1-1-1) on Si(110). Diamond and Related Materials, 2016, 67, 51-53.	3.9	6
22	Interfacial Charge States in Graphene on SiC Studied by Noncontact Scanning Nonlinear Dielectric Potentiometry. Physical Review Letters, 2015, 114, 226103.	7.8	31
23	Microscopically-Tuned Band Structure of Epitaxial Graphene through Interface and Stacking Variations Using Si Substrate Microfabrication. Scientific Reports, 2015, 4, 5173.	3.3	13
24	Highly Brilliant Synchrotron Radiation Operando Spectromicroscopy to Bridge a Gap between Material Electronic Properties and Device Performances of 2D Atomic Layers. Hyomen Kagaku, 2015, 36, 303-308.	0.0	0
25	Observing hot carrier distribution in an n-type epitaxial graphene on a SiC substrate. Applied Physics Letters, 2014, 104, .	3.3	65
26	Pinpoint operando analysis of the electronic states of a graphene transistor using photoelectron nanospectroscopy. Applied Physics Express, 2014, 7, 065101.	2.4	13
27	Orbital-specific Tunability of Many-Body Effects in Bilayer Graphene by Gate Bias and Metal Contact. Scientific Reports, 2014, 4, 3713.	3.3	28
28	Operando Spectromicroscopy Observation of Many-Body Effects in Graphene Device. The Review of Laser Engineering, 2014, 42, 633.	0.0	0
29	Direct observation of charge transfer region at interfaces in graphene devices. Applied Physics Letters, 2013, 102, .	3.3	33
30	Discharge Instability at Patterned Conductive Layers on Insulating Substrates during Pulsed-Plasma Chemical Vapor Deposition under Near Atmospheric Pressures. E-Journal of Surface Science and Nanotechnology, 2013, 11, 47-52.	0.4	0
31	Transmission-Electron-Microscopy Observations on the Growth of Epitaxial Graphene on 3C-SiC(110) and 3C-SiC(100) Virtual Substrates. Materials Science Forum, 2012, 711, 242-245.	0.3	2
32	Nanoscale Control of Structural and Electronic Properties of Graphene through Substrate Interaction. Hyomen Kagaku, 2012, 33, 546-551.	0.0	0
33	Carbonaceous field effect transistor with graphene and diamondlike carbon. Diamond and Related Materials, 2012, 22, 118-123.	3.9	21
34	Graphene-based devices in terahertz science and technology. Journal Physics D: Applied Physics, 2012, 45, 303001.	2.8	234
35	Graphene materials and devices in terahertz science and technology. MRS Bulletin, 2012, 37, 1235-1243.	3.5	30
36	Control of epitaxy of graphene by crystallographic orientation of a Si substrate toward device applications. Journal of Materials Chemistry, 2011, 21, 17242.	6.7	37

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37	Observation of Amplified Stimulated Terahertz Emission from Optically Pumped Heteroepitaxial Graphene-on-Silicon Materials. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , 2011, 32, 655-665.	2.2	41
38	Controls over Structural and Electronic Properties of Epitaxial Graphene on Silicon Using Surface Termination of 3C-SiC(111)/Si. <i>Applied Physics Express</i> , 2011, 4, 115104.	2.4	39
39	Visualization of Single Atomic Steps on An Ultra-Flat Si(100) Surface by Advanced Differential Interference Contrast Microscopy. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, H351.	2.2	8
40	Epitaxial graphene top-gate FETs on silicon substrates. <i>Solid-State Electronics</i> , 2010, 54, 1071-1075.	1.4	18
41	Surface Chemistry Involved in Epitaxy of Graphene on 3C-SiC(111)/Si(111). <i>Nanoscale Research Letters</i> , 2010, 5, 1888-1891.	5.7	30
42	(Invited) Epitaxial Formation of Graphene on Si Substrates: From Heteroepitaxy of 3C-SiC to Si Sublimation. <i>ECS Transactions</i> , 2010, 33, 859-867.	0.5	0
43	Epitaxial graphene on silicon substrates. <i>Journal Physics D: Applied Physics</i> , 2010, 43, 374012.	2.8	107
44	Graphene-on-Silicon Formation by Thermal Conversion of 3C-SiC Thin Films on Si(111), (110), (100) Substrates. <i>Hyomen Kagaku</i> , 2010, 31, 352-358.	0.0	3
45	Raman-Scattering Spectroscopy of Epitaxial Graphene Formed on SiC Film on Si Substrate. <i>E-Journal of Surface Science and Nanotechnology</i> , 2009, 7, 107-109.	0.4	63
46	Microscopic Changes of Thin Films of Directly Thiolated Fullerenes Depending on Substrate and Number of Thiol. <i>Japanese Journal of Applied Physics</i> , 2007, 46, 5560.	1.5	1
47	Interaction of cesium with charged oxide under UV irradiation imaged by photoemission electron microscopy. <i>Surface Science</i> , 2007, 601, 5309-5312.	1.9	1
48	Microscopically controlled oxidation of H/Si(100) by lateral surface electric field studied by emission electron microscopies. <i>Surface Science</i> , 2007, 601, 4675-4679.	1.9	3
49	Evaporation and Thermionic Emission Processes of Pb/W(110) Imaged In Situ by Emission Electron Microscopy. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 70-72.	1.5	2
50	Variation of Contrast of H/pn-Si(100) Imaged with Different Emission Electron Microscopies. <i>E-Journal of Surface Science and Nanotechnology</i> , 2006, 4, 539-543.	0.4	2
51	Temperature-Dependent Contrasts of Lateral p-n Junctions on H/Si(100) Imaged with Photoemission Electron Microscopy. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L1417-L1419.	1.5	2
52	Scanning Tunneling Microscopy Study of Water Molecules on Pd(110) at Cryogenic Temperature. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 4932-4935.	1.5	10
53	Characteristic Configuration of Cis-2-butene Molecule on Pd(110) Determined by Scanning Tunneling Microscopy. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 4976-4979.	1.5	6
54	In-Situ FTIR Studies of Reactions at the Silicon/Liquid Interface: Wet Chemical Etching of Ultrathin SiO ₂ on Si(100). <i>Journal of Physical Chemistry B</i> , 2001, 105, 3903-3907.	2.6	43

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55	Effect of dissolved oxygen on etching process of Si(111) in 2.5% NH ₃ solution. Surface Science, 2000, 463, L649-L653.	1.9	21
56	In Situ Atomic Force Microscopy Observation of Dissolution Process of Si(111) in Oxygen-Free Water at Room Temperature. Electrochemical and Solid-State Letters, 1999, 2, 393.	2.2	16
57	A Very Simple Method of Flattening Si(111) Surface at an Atomic Level Using Oxygen-Free Water. Japanese Journal of Applied Physics, 1999, 38, L1085-L1086.	1.5	42
58	Analysis of Silicon Surface in Connection with Its Unique Electrochemical and Etching Behavior. Journal of the Electrochemical Society, 1997, 144, 679-682.	2.9	7
59	Enhanced Etching Rate of Silicon in Fluoride Containing Solutions at pH 6.4. Journal of the Electrochemical Society, 1996, 143, 2683-2686.	2.9	26